

and a laser light.

*SUB F1* 47. (Amended) A method according to claim 45, wherein said semiconductor flim is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

48. (Amended) A method according to claim 45, wherein said gate insulating film is continuously formed without exposing to the air after forming said semiconductor film.

*SUB E2*  
*D1*  
*cont* 49. (Amended) A method for manufacturing a semiconductor device comprising steps of:  
contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;  
subjecting said semiconductor film to plasma comprising oxygen and helium; and  
irradiating said semiconductor film subjected to the plasma with one of an infrared ray and a laser light.

50. (Amended) A method according to claim 49, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

*SUB E3*  
*D2* 52. (Amended) 322A method for manufacturing a semiconductor device comprising steps of:  
contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;  
subjecting said semiconductor film to oxygen plasma; and  
crystallizing said semiconductor film subjected to the oxygen plasma using said material, to obtain a crystalline semiconductor film.

53. (Amended) A method according to claim 52, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.

D2  
cont

54. (Amended) A method according to claim 52, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

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SUB E4 >  
D3

56. (Amended) A method for manufacturing a semiconductor device comprising steps of:

- contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;
- subjecting said semiconductor film to oxygen plasma;
- irradiating said semiconductor film subjected to the oxygen plasma with one of an infrared ray and a laser light; and
- patterning said crystalline semiconductor film.

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D4

58. (Amended) A method according to claim 56, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

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SUB E5 >  
D5

60. (Amended) A method for manufacturing a semiconductor device comprising steps of:

- contacting at least one metal element to at least a part of a semiconductor film formed over a substrate;
- subjecting said semiconductor film to plasma;
- crystallizing said semiconductor film subjected to the oxygen plasma to obtain a crystalline semiconductor film; and
- patterning said crystalline semiconductor film.

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61. (Amended) A method according to claim 60, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.